Schottky Barrier Diodes

BAS40L, SBAS40L

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

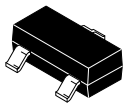
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Forward Power Dissipation @ T_A = 25°C Derate above 25°C	P_F	 225 1.8	 mW mW/°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Forward Continuous Current	I_F	120	mA
Forward Surge Current t ≤ 1 s t ≤ 10 ms	I_{FSM}	 200 600	mA
Thermal Resistance (Note 1) Junction−to−Ambient (Note 2)	$R_{\theta JA}$	508 311	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−4 @ minimum pad.
2. FR−4 @ 1.0 x 1.0 in pad.

40 VOLTS
SCHOTTKY BARRIER DIODES



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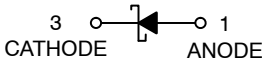
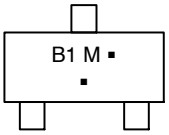
STYLE 8



MARKING DIAGRAM



B1 = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAS40LT1G, SBAS40LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BAS40LT3G, SBAS40LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μA)	$V_{(BR)R}$	40	–	V
Total Capacitance (V_R = 1.0 V, f = 1.0 MHz)	C_T	–	5.0	pF
Reverse Leakage (V_R = 25 V)	I_R	–	1.0	μAdc
Forward Voltage (I_F = 1.0 mAdc)	V_F	–	380	mVdc
Forward Voltage (I_F = 10 mAdc)	V_F	–	500	mVdc
Forward Voltage (I_F = 40 mAdc)	V_F	–	1.0	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

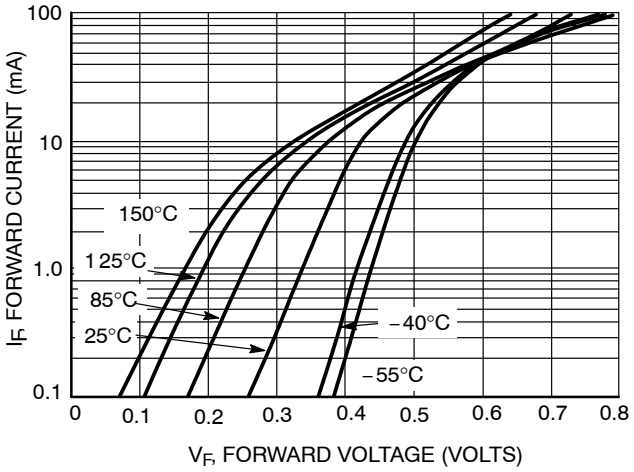


Figure 1. Typical Forward Voltage

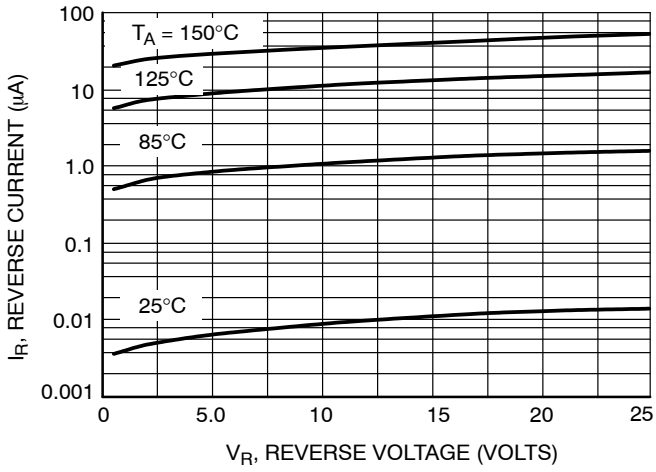


Figure 2. Reverse Current versus Reverse Voltage

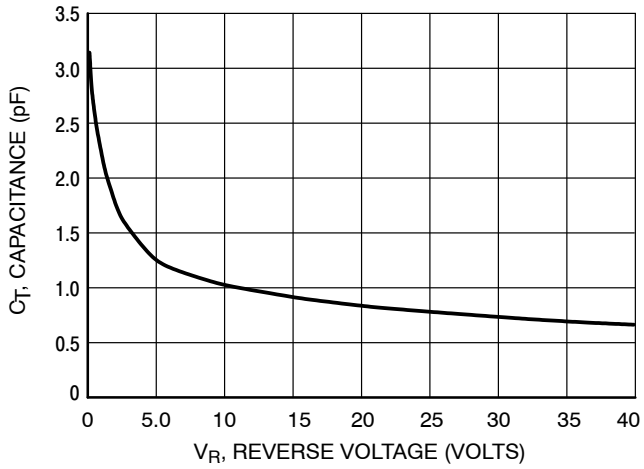
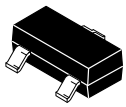


Figure 3. Typical Capacitance

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

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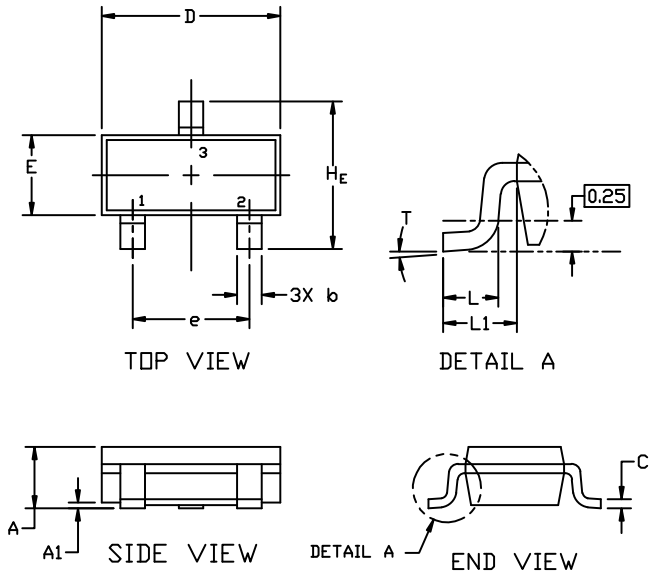
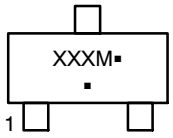


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

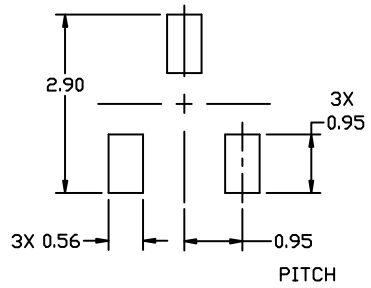
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

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STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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